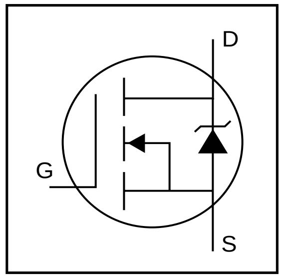
International
IOR Rectifier

PD - 91325C

IRL2505

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



V_{DSS} = 55V

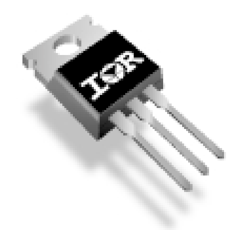
$R_{DS(on)}$ = 0.008Ω

I_D = 104A⑤

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 is universally preferred for all commercial-Industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	104⑤	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	74	
I_{DM}	Pulsed Drain Current ①	360	
P_D @T_C = 25°C	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy②	500	mJ
I_{AR}	Avalanche Current ①	54	A
E_{AR}	Repetitive Avalanche Energy①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

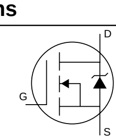
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	
$R_{\theta JA}$	Juction-to-Ambient	——	62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.035	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.008	Ω	V_{GS} = 10V, I_D = 54A ④
		——	——	0.010		V_{GS} = 5.0V, I_D = 54A ④
		——	——	0.013		V_{GS} = 4.0V, I_D = 45A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	59	——	——	S	V_{DS} = 25V, I_D = 54A
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	µA	V_{DS} = 55V, V_{GS} = 0V
		——	——	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -16V
Q_g	Total Gate Charge	——	——	130	nC	I_D = 54A
Q_{gs}	Gate-to-Source Charge	——	——	25		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	67		V_{GS} = 5.0V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	——	12	——	ns	V_{DD} = 28V
t_r	Rise Time	——	160	——		I_D = 54A
$t_{d(off)}$	Turn-Off Delay Time	——	43	——		R_G = 1.3Ω, V_{GS} = 5.0V
t_f	Fall Time		84	-		R_D = 0.50Ω, See Fig. 10 ④
L_S	Internal Source Inductance	——	7.5	——	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	——	5000	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	1100	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	390	——		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	104⑤	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	360		
V_{SD}	Diode Forward Voltage	——	——	1.3	V	T_J = 25°C, I_S = 54A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	140	210	ns	T_J = 25°C, I_F = 54A
Q_{rr}	Reverse Recovery Charge	——	650	970	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 240µH R_G = 25Ω, I_{AS} = 54A. (See Figure 12)

③ $I_{SD} \le$ 54A, di/dt ≤ 230A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ Calculated continuous current based on maximum allowable junction temperature;for recommended current-handling of the package refer to Design Tip # 93-4

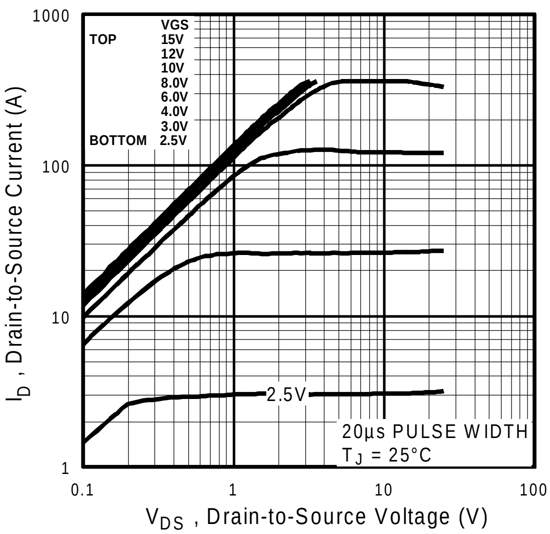


Fig 1. Typical Output Characteristics

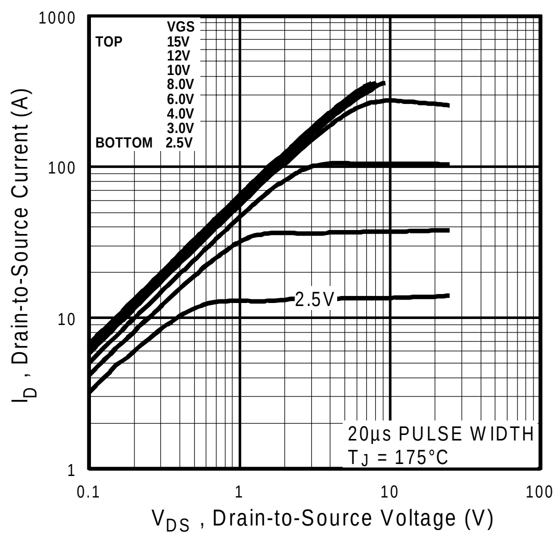


Fig 2. Typical Output Characteristics

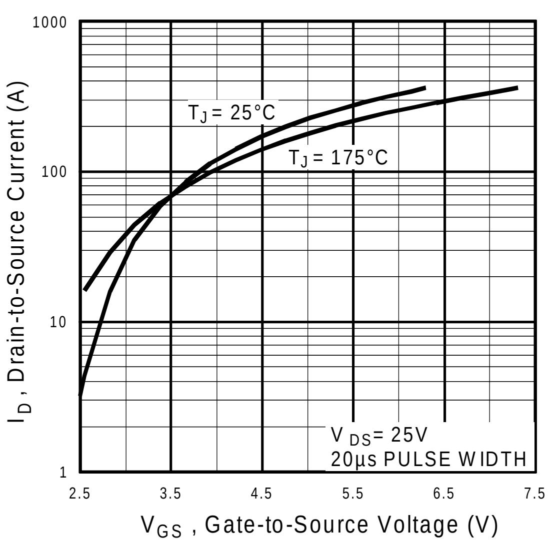


Fig 3. Typical Transfer Characteristics

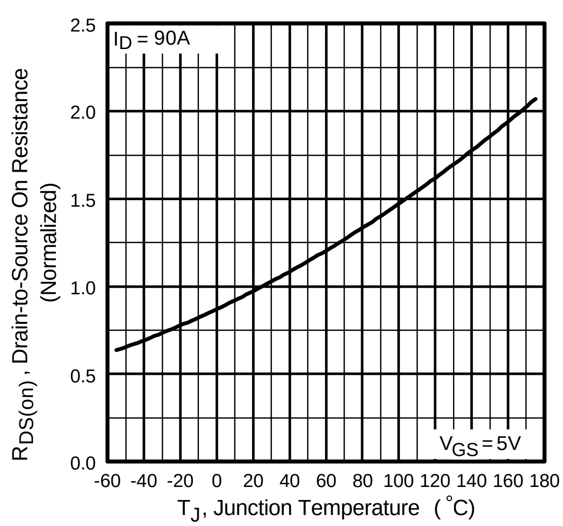


Fig 4. Normalized On-Resistance Vs. Temperature

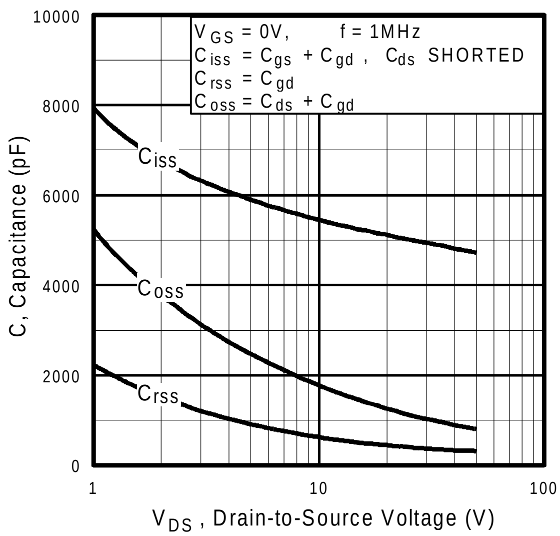


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

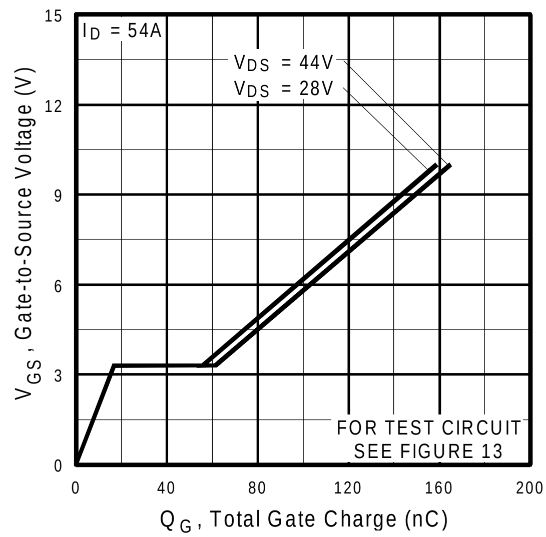


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

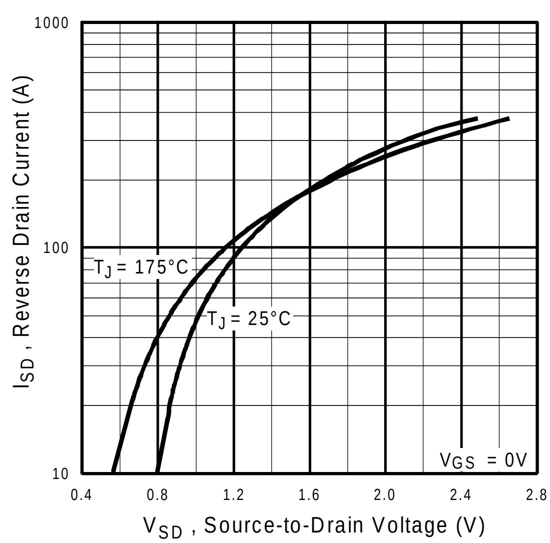


Fig 7. Typical Source-Drain Diode Forward Voltage

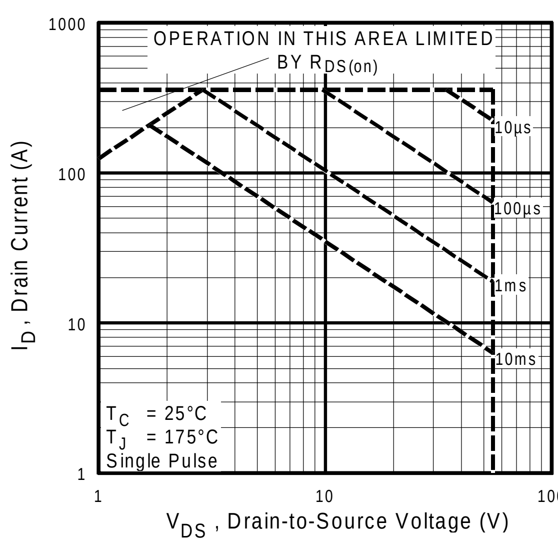


Fig 8. Maximum Safe Operating Area

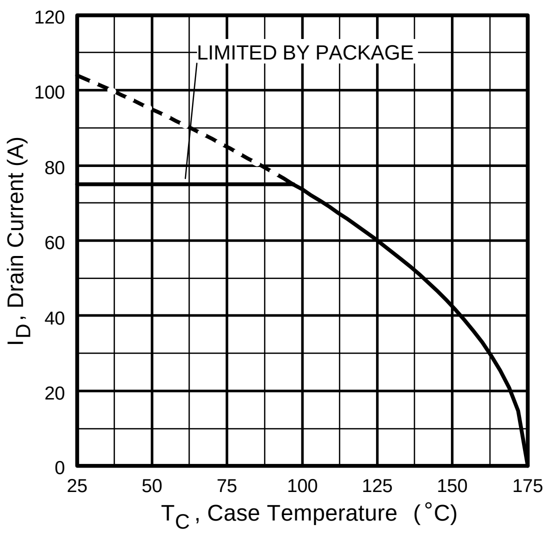


Fig 9. Maximum Drain Current Vs. Case Temperature

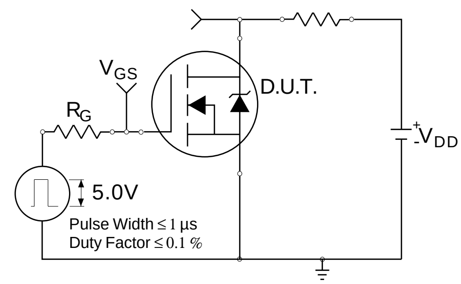


Fig 10a. Switching Time Test Circuit

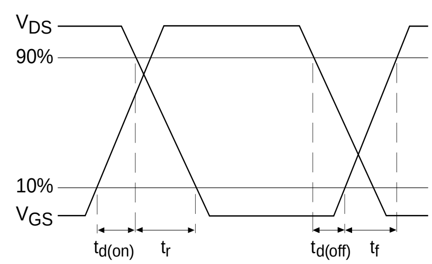


Fig 10b. Switching Time Waveforms

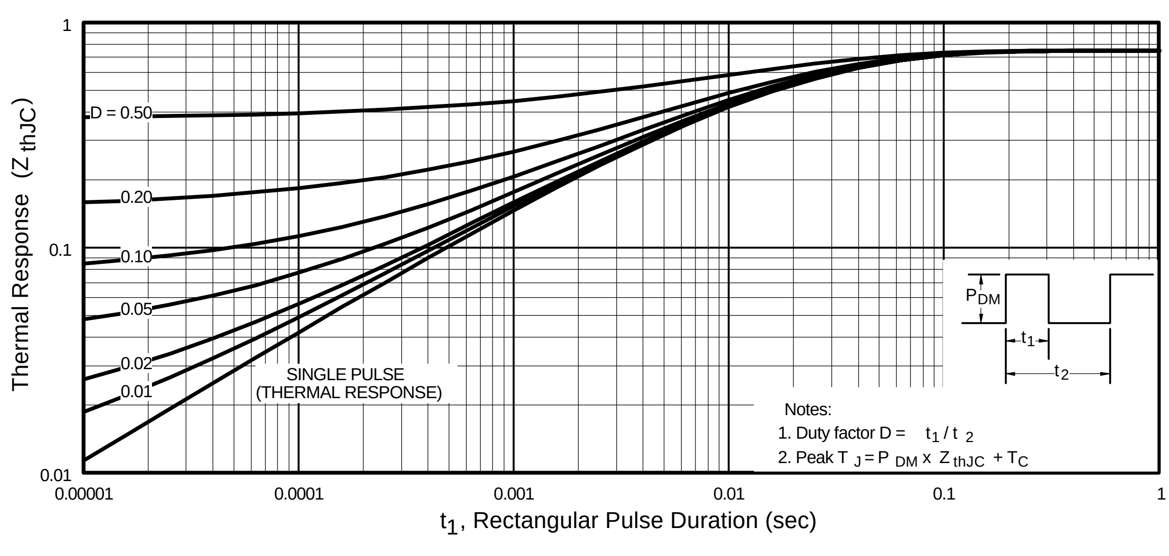


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

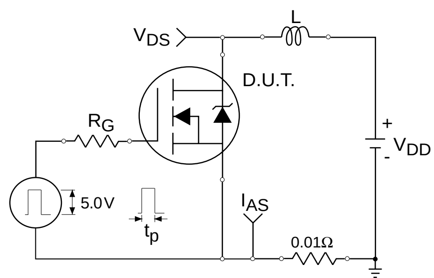


Fig 12a. Unclamped Inductive Test Circuit

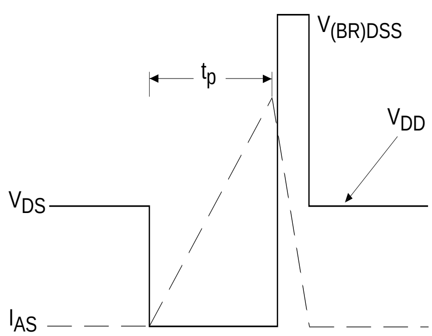


Fig 12b. Unclamped Inductive Waveforms

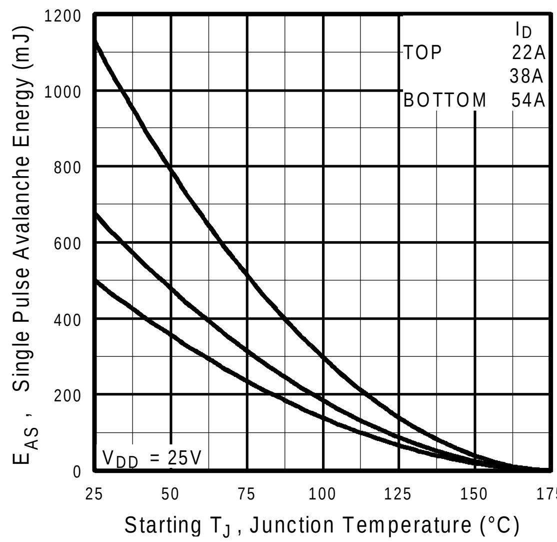


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

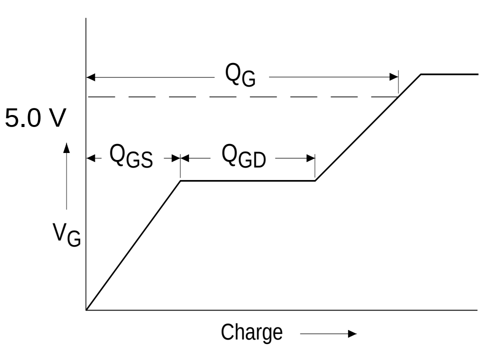


Fig 13a. Basic Gate Charge Waveform

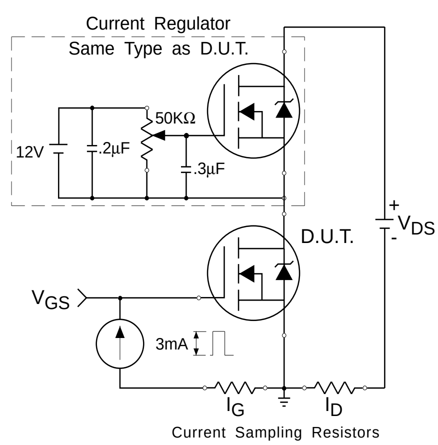
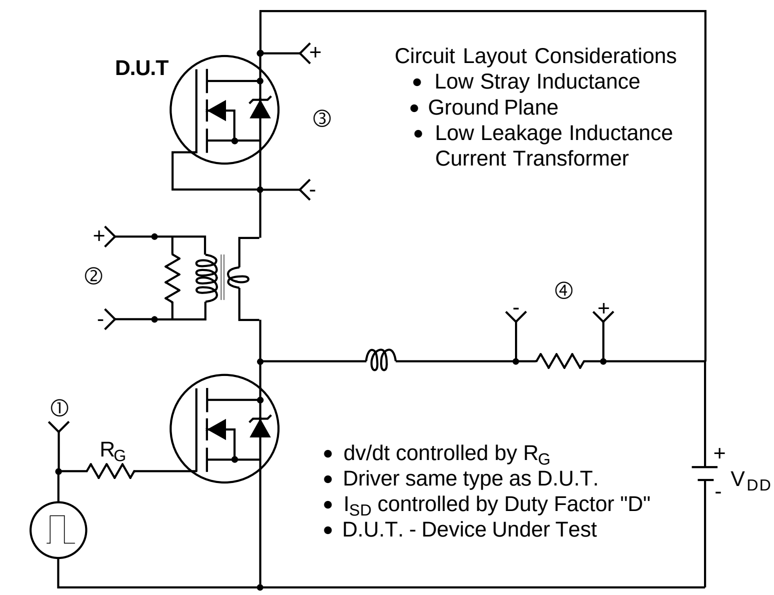
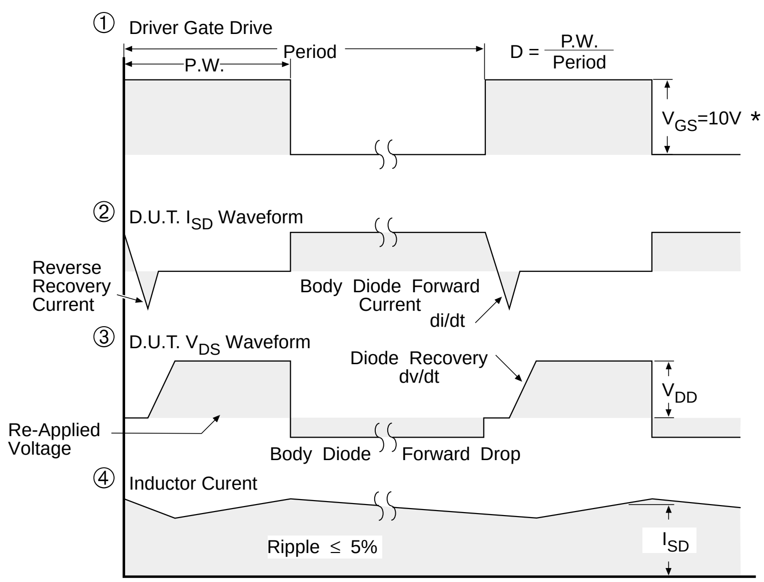


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



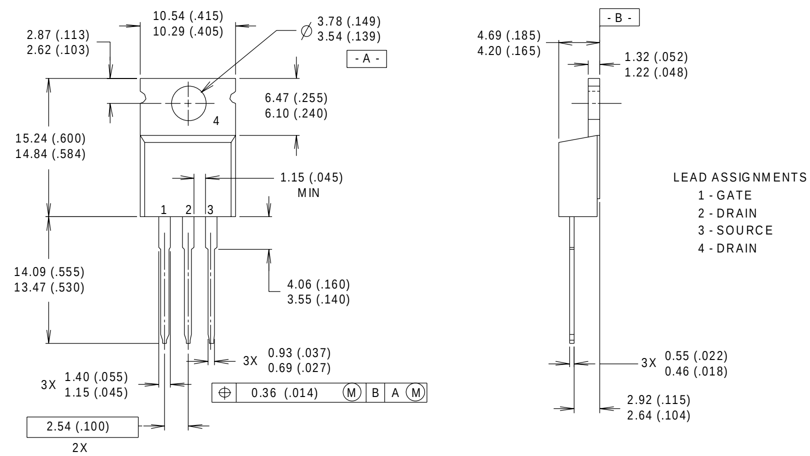


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

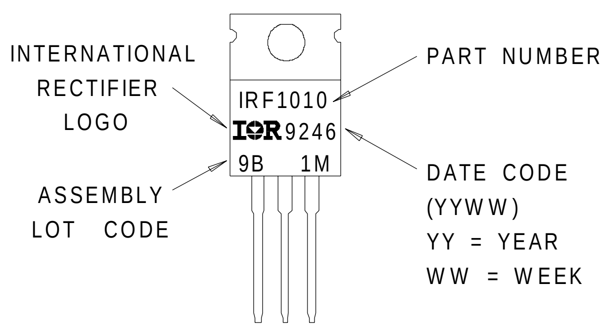


NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE : THIS IS AN IRF1010
WITH ASSEMBLY
LOT CODE 9B1M



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market
Qualification Standards can be found on IR's Web site.

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Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/